

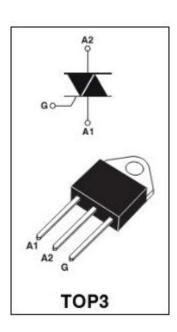
isc Triacs BTA26-600B

## **FEATURES**

- With TO-3P insulated package
- Suitable for general purpose where high surge current capability is required. application such as phase control and static switching on inductive or resistive load.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

ABOOLOTE MAXIMOM (ATTIVOS)								
PARAMETER	MIN	UNIT						
Repetitive peak off-state voltage	600	V						
Repetitive peak reverse voltage	600	V						
RMS on-state current (full sine wave))Tj=90°C	25	Α						
Non-repetitive peak on-state current t <sub>p</sub> =8.3ms	260	Α						
Operating junction temperature	125	$^{\circ}$						
Storage temperature	-45~150	$^{\circ}$						
Average gate power dissipation(T <sub>j</sub> =125℃)	1	W						
Thermal resistance, junction to case	1.5	°C/W						
Thermal resistance, junction to ambient	50	°C/W						
	PARAMETER  Repetitive peak off-state voltage  Repetitive peak reverse voltage  RMS on-state current (full sine wave))Tj=90°C  Non-repetitive peak on-state current tp=8.3ms  Operating junction temperature  Storage temperature  Average gate power dissipation(Tj=125°C)  Thermal resistance, junction to case	PARAMETERMINRepetitive peak off-state voltage $600$ Repetitive peak reverse voltage $600$ RMS on-state current (full sine wave)) $T_j=90^{\circ}$ $25$ Non-repetitive peak on-state current $t_p=8.3ms$ $260$ Operating junction temperature $125$ Storage temperature $-45\sim150$ Average gate power dissipation( $T_j=125^{\circ}$ C) $1$ Thermal resistance, junction to case $1.5$						



## **ELECTRICAL CHARACTERISTICS (Tc=25℃ unless otherwise specified)**

SYMBOL	PARAMETER		CONDITIONS	MAX	UNIT
I <sub>RRM</sub>	Repetitive peak reverse current		VR=VRRM, VR=VRRM, Tj=125°C	0.01 6.0	mA
I <sub>DRM</sub>	Repetitive peak off-state current		$V_D = V_{DRM}$ , $V_D = V_{DRM}$ , $T_J = 125$ $^{\circ}$ C	0.01 6.0	mA
I <sub>GT</sub> Gate trigger current		Ι		50	
	II	- V <sub>D</sub> =12V; R <sub>L</sub> = 33 Ω	50	- mA	
	III		50		
	IV		100		
lμ	Holding current		I <sub>GT</sub> = 0.5A, Gate Open	80	mA
V <sub>GT</sub>	Gate trigger voltage all quadrant		V <sub>D</sub> =12V; R <sub>L</sub> = 33 Ω	1.5	V
$V_{TM}$	On-state voltage		I <sub>T</sub> = 35A; t <sub>p</sub> = 380 μ s	1.7	V



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